

isc N-Channel MOSFET Transistor

STP65NF06

• FEATURES

- · With TO-220 packaging
- · High speed switching
- Standard level gate drive
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Power supply
- · Switching applications

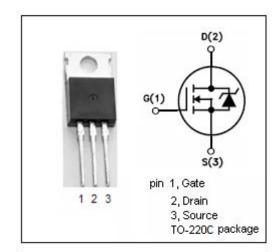


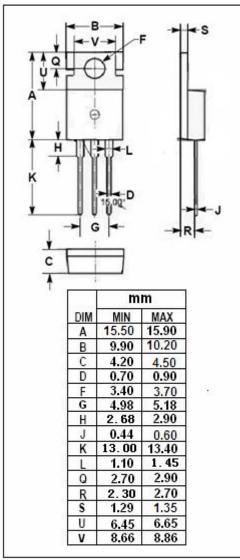
• ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|----------|------------|--|
| V _{DSS} | Drain-Source Voltage | 60 | V | |
| V _{GSS} | Gate-Source Voltage | ±20 | V | |
| I _D | $\begin{array}{c} \text{Drain Current-Continuous@T}_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!$ | 60 42 | А | |
| I _{DM} | Drain Current-Single Pulsed | 240 | А | |
| P _D | Total Dissipation | 110 | W | |
| Tj | Operating Junction Temperature | -55~175 | $^{\circ}$ | |
| T _{stg} | Storage Temperature | -55~175 | $^{\circ}$ | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT | |
|-----------|---------------------------------------|------|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 1.36 | °C/W | |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 62.5 | °C/W | |







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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|-----------------------------------------------------------------|-----|------|---------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 60 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =±20V; I _D =0.25mA | 2 | | 4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =30A | | 11.5 | 14 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} = 0V | | | ±0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 60V; V _{GS} = 0V;Tc=25°C Tc=125°C | | | 1 10 | μА |
| V _{SDF} | Diode forward voltage | I _{SD} =60A, V _{GS} = 0 V | | | 1.5 | V |

NOTICE:

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